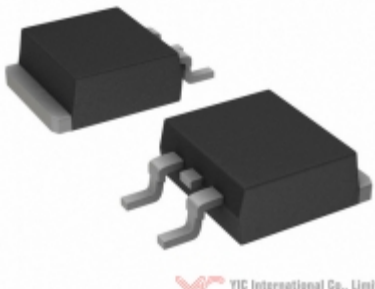

	<h2 style="color: red;">FQB4N80TM</h2>
 <p>Image may be representation. See specs for product details.</p>	<b>Hersteller-Teilenummer:</b> <a href="#">FQB4N80TM</a>
	<b>Hersteller / Marke:</b> <a href="#">Fairchild/ON Semiconductor</a>
	<b>Teil der Beschreibung:</b> MOSFET N-CH 800V 3.9A D2PAK
	<b>Datenblätter:</b>  <a href="#">FQB4N80TM.pdf</a>
	<b>RoHs Status:</b> Bleifrei / RoHS-konform
	<b>Lagerzustand:</b> New original, 35616 pcs Stock Available.
	<b>Liefern von:</b> Hong Kong
<b>Versandweg:</b> DHL/Fedex/TNT/UPS/EMS	

### Spezifikationen

Teilenummer	<a href="#">FQB4N80TM</a>
Hersteller	<a href="#">Fairchild/ON Semiconductor</a>
Beschreibung	MOSFET N-CH 800V 3.9A D2PAK
Kategorie	<a href="#">Diskrete Halbleiterprodukte &gt; Transistoren-FETs,</a>
Teilstatus	35616 pcs Stock
Serie	QFET®
Technologie	MOSFET (Metal Oxide)
Betriebstemperatur	-55°C ~ 150°C (TJ)
Befestigungsart	Surface Mount
Verpackung / Gehäuse	TO-263-3, D <sup>2</sup> Pak (2 Leads + Tab), TO-263AB
Supplier Device-Gehäuse	D <sup>2</sup> PAK (TO-263AB)
Verlustleistung (max)	3.13W (Ta), 130W (Tc)
Typ FET	N-Channel
FET-Merkmal	-
Drain-Source-Spannung (Vdss)	800V
Strom - Ununterbrochener Abfluss (Id) bei 25 °C	3.9A (Tc)
Rds On (Max) @ Id, Vgs	3.6 Ohm @ 1.95A, 10V
VGS (th) (Max) @ Id	5V @ 250µA
Gate Charge (Qg) (Max) @ Vgs	25nC @ 10V
Eingabekapazität (Ciss) (Max) @ Vds	880pF @ 25V
Antriebsspannung (Max Rds On, Min Rds On)	10V
Vgs (Max)	±30V
Verpackung	Tape & Reel (TR)











































FQB4N80TM ist neu im Original, Suche FQB4N80TM Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie FQB4N80TM Fairchild/ON Semiconductor mit Garantie und Vertrauen. Anfrage FQB4N80TM: [Info@Y-IC.com](mailto:Info@Y-IC.com)

Sie können auch interessiert sein:

 <p><b>FQB4N90TM</b> AMI Semiconductor / ON Semiconductor MOSFET N-CH 900V 4.2A D2PAK</p>	 <p><b>FQB4P25TM</b> Fairchild/ON Semiconductor MOSFET P-CH 250V 4A D2PAK</p>	 <p><b>FQB4N60</b> Fairchild/ON Semiconductor FQB4N60 FAIRCHILD</p>	 <p><b>FQB4N60C</b> FAIRCHI FQB4N60C FAIRCHI</p>
 <p><b>FQB4N80TM</b> AMI Semiconductor / ON Semiconductor MOSFET N-CH 800V 3.9A D2PAK</p>	 <p><b>FQB4N90TM</b> Fairchild/ON Semiconductor MOSFET N-CH 900V 4.2A D2PAK</p>	 <p><b>FQB4N90(SSW4N90A)</b> FAIRCHILD FAIRCHILD SOT-263</p>	 <p><b>FQB4N80</b> FAIRCHILD FQB4N80 FAIRCHILD</p>

### heiße Teile

Mehr

 FQB3N90TM	 FQB3N90TM	 FQB3P20TM	 FQB3P20TM	 FQB3P50TM
 FQB3P50TM	 FQB44N10	 FQB44N10TM	 FQB44N10TM	 FQB46N15
 FQB46N15TM	 FQB47P06	 FQB47P06TM	 FQB4N20L	 FQB4N20LTM
 FQB4N20LTM	 FQB4N20TM	 FQB4N20TM	 FQB4N25TM	 FQB4N25TM
 FQB4N20TM	 FQB4N50TM	 FQB4N50TM	 FQB4N60C	 FQB4N80TM
 FQB4N90TM	 FQB4N90TM	 FQB4P25TM	 FQB4P25TM	 FQB50N03
 FQB50N06	 FQB50N06C	 FQB50N06L	 FQB50N06LTM	 FQB50N06LTM
 FQB50N06M	 FQB50N06TM	 FQB50N06TM	 FQB50N06TM-NL	 FQB55N06TM
 FQB55N06TM	 FQB55N10	 FQB55N10TM	 FQB55N10TM	 FQB5N20L
 FQB5N30TM	 FQB5N30TM	 FQB5N50C	 FQB5N50CF	 FQB5N50CTM

Contact us: [Info@Y-IC.com](mailto:Info@Y-IC.com)

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